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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 4

Complete if Known

Application Number	10/550,855
Filing Date	
First Named Inventor	VON KAENEL, Hans
Art Unit	1734
Examiner Name	
Attorney Docket Number	PUS-E005-013

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US- 6,454,855	09/24/2002	VON KAENEL et al.	entire document
		US- 2002/0056414	05/16/2002	SHIM et al.	entire document
		US- 2002/0139996	10/03/2002	JAGANNATHAN	entire document
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FOREIGN PATENT DOCUMENTS

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		EP 1 315 199	05/28/2003	VON KAENEL	entire document	
		WO/1998/058099	12/23/1998	VON KAENEL et al.	entire document	
		WO/2003/044839	05/30/2003	VON KAENEL	entire document	

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	1	KASPER et al., New virtual substrate concept for vertical MOS transistors, Thin Solid Films, Vol. 336, p. 319-22 (1998)	
	2	BAUER et al., Relaxed SiGe buffers with thicknesses below 0.1 um, Thin Solid Films, Vol. 369, p. 152-56 (2000)	
	3	HACKBARTH et al., Alternatives to thick MBE-grown relaxed SiGe buffers, Thin Solid Films, Vol. 369, p. 148-51 (2000)	
	4	UENO et al., Low temperature buffer growth for modulation doped SiGe/Ge/SiGe heterostructures with high hole mobility, Thin Solid Films, Vol. 369, p. 320-23 (2000)	
	5	KUCHENBECKER et al., Thin SiGe buffer layer growth by in situ low energy hydrogen plasma preparation, Thin Solid Films, Vol. 389, p. 146-52 (2001)	
	6	FITZGERALD et al., Totally relaxed GeXSi1-X layers with low threading dislocation densities grown on Si substrates, Appl. Phys. Lett., Vol. 59, p. 811-13 (1991)	
	7	ISMAIL et al., Extremely high electron mobility in Si/SiGe modulation-doped heterostructures, Appl. Phys. Lett., Vol. 66, p. 1077-79 (1995)	
	8	LINDER et al., Reduction of dislocation density in mismatched SiGe/Si using a low-temperature Si buffer layer, Appl. Phys. Lett., Vol. 70, p. 3224-26 (1997)	
	9	LI et al., Relaxed Si0.7Ge0.3 layers grown on low-temperature Si buffers with low threading dislocation density, Appl. Phys. Lett., Vol. 71, p. 3132-34 (1997)	
	10	PENG et al., Relaxed Ge0.9Si0.1 alloy layers with low threading dislocation densities grown on low-temperature Si buffers, Appl. Phys. Lett., Vol. 72, p. 3160-62 (1998)	

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	11	ROSENBLAD et al., A plasma process for ultrafast deposition of SiGe graded buffer layers, Appl. Phys. Lett., Vol 76, p. 427-29 (2000)	
	12	VON KAENEL et al., Very high hole mobilities in modulation-doped Ge quantum wells grown by low-energy plasma enhanced chemical vapor deposition,	
		Appl. Phys. Lett., Vol. 80, p. 2922-24 (2002)	
	13	MUROTA et al., Low-Temperature Epitaxial Growth of Si/Si1-XGeX/Si Heterostructure by Chemical Vapor Deposition, Jpn. J. Appl. Phys., Vol. 33, p. 2290-99 (1994)	
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	15	WEITZ et al., Tilted magnetic field studies of spin- and valley-splittings in Si/Si1-XGeX heterostructures, Surf. Sci., Vol. 361/362, p. 542-46 (1996)	
	16	SCHUEGRAF et al., Handbook of thin-film deposition processes and techniques, Noyes Publications, New Jersey, US, p. 26-79 article by M.L. HAMMOND (1988)	
	17	MANTL et al., Strain relaxation of epitaxial SiGe layers on Si(100) improved by hydrogen implantation, Nucl. Instr. and Meth. in Phys. Res., Vol. B 147, p. 29-34 (1999)	
	18	HOLLAENDER et al., Enhanced strain relaxation of epitaxial SiGe layers on Si(100) after H+ ion implantation,	
		Nucl. Instr. and Meth. in Phys. Res., Vol. B 148, p. 200-05, (1999)	

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	19	HOLLAENDER et al., Strain relaxation of pseudomorphic Si1-XGeX/Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication,	
		Nucl. Instr. and Meth. in Phys. Res., Vol. B 175-177, p. 357-67 (2001)	
	20	HERZOG et al., Si/SiGe n-MODFETs on Thin SiGe Virtual Substrates Prepared by Means of He Implantation, IEEE Electron Device Letters, Vol. 23, p. 485-87 (2002)	
	21	LYUTOVICH et al., Thin SiGe buffers with high Ge content for n-MOSFETs, Materials Science and Engineering, Vol. B89, p. 341-45 (2002)	

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